

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Specification.

Please insert the following paragraph beginning on page 12, line 8.

a1  
FIG. 4 is a cross-sectional view of a portion of a DRAM after various processing steps according to an embodiment.

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Please replace the paragraph beginning on page 2, line 15 with the following.

a2  
A first interlayer insulating film **26** is formed on word line **22**. A cell contact hole is formed between word lines **22** to expose the silicon substrate **12** through first interlayer insulating film **26**. Cell contact hole is filled with an electrically conductive material  
10 such as DOPOS and tungsten (W) to form a cell contact plug **30**.